

SPTECH Field Stop Trench IGBTs offer low switching losses, high energy efficiency and high avalanche ruggedness for soft switching applications such as inductive heating, microwave oven, etc.

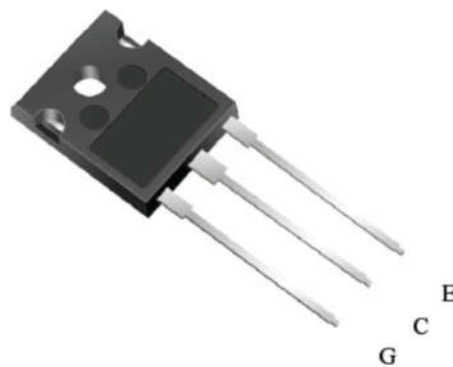
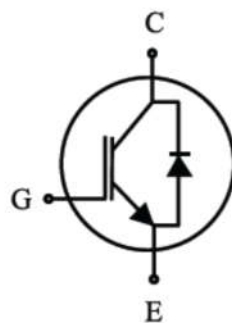
V_{CE}	1350	V
I_C	25	A
$V_{CE(SAT)} \quad I_C=25A$	2.0	V

FEATURES

- High breakdown voltage to 1350V for improved reliability
- Trench-Stop Technology offering :
 - High speed switching
 - High ruggedness, temperature stable
 - Low V_{CEsat}
 - Easy parallel switching capability due to positive temperature coefficient in V_{CEsat}
- Soft current turn-off waveforms
- Enhanced avalanche capability

APPLICATION

- Inductive cooking
- Inverterized microwave ovens
- Resonant converters
- Soft switching applications



Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter Breakdown Voltage	V_{CE}	1350	V
DC collector current, limited by T_{jmax} $T_C = 25^{\circ}C$ $T_C = 100^{\circ}C$	I_C	50 25	A
Diode Forward current, limited by T_{jmax} $T_C = 25^{\circ}C$ $T_C = 100^{\circ}C$	I_F	50 25	A
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	75	A
Turn off safe operating area $V_{CE} \leq 1350V$, $T_j \leq 150^{\circ}C$	-	75	A
Operating junction temperature T_j	-	-40...+150	$^{\circ}C$
Storage temperature	T_s	-55...+150	$^{\circ}C$
Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s	-	260	$^{\circ}C$

Thermal Resistance

Parameter	Symbol	Max. Value	Unit
IGBT thermal resistance, junction - case	$R_{\theta(j-c)}$	0.48	K/W
Diode thermal resistance, junction - case	$R_{\theta(j-c)}$	1.2	K/W
Thermal resistance, junction - ambient	$R_{\theta(j-a)}$	40	K/W



Electrical Characteristics of the IGBT ($T_j = 25^\circ\text{C}$ unless otherwise specified) :

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Static						
Collector-Emitter breakdown voltage	BV_{CES}	$V_{GE}=0V, I_C=1mA$	1350	1450	-	V
		$V_{GE}=0V, I_C=10mA$	1350	1450	-	V
Gate threshold voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=250\mu A$	5.1	5.8	6.4	V
Collector-Emitter Saturation voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=25A$ $T_j = 25^\circ\text{C}$	-	2.0	2.5	V
		$T_j = 150^\circ\text{C}$	-	2.5	-	
Zero gate voltage collector current	I_{CES}	$V_{CE} = 1350V, V_{GE} = 0V$ $T_j = 25^\circ\text{C}$	-	<1	100	μA
		$T_j = 150^\circ\text{C}$	-	-	1000	
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0V, V_{GE} = 20V$	-	-	100	nA

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Dynamic						
Input capacitance	C_{ies}	$V_{CE} = 25V, V_{GE} = 0V,$ $f = 1MHz$	-	2500	-	pF
Output capacitance	C_{oes}		-	70	-	
Reverse transfer capacitance	C_{res}		-	50	-	
Gate charge	Q_G	$V_{CC} = 600V, I_C = 25A,$ $V_{GE} = 15V$	-	125	-	nC

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Dynamic , at T _j = 25° C						
Turn-off delay time	td _(off)	V _{CC} = 600V, I _C = 25A, V _{GE} = 0/15V, R _g =10Ω	-	180	-	ns
Fall time	t _f		-	40	-	ns
Turn-off energy	E _{off}		-	0.32	-	mJ
Dynamic , at T _j = 150° C						
Turn-off delay time	td _(off)	V _{CC} = 600V, I _C = 25A, V _{GE} = 0/15V, R _g =10Ω	-	220	-	ns
Fall time	t _f		-	90	-	ns
Turn-off energy	E _{off}		-	0.65	-	mJ



Electrical Characteristics of the DIODE ($T_j = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Dynamic						
Diode Forward Voltage	V_{FM}	$I_F = 25\text{A}$	-	2.3	-	V
Reverse Recovery Time	T_{rr}	$I_F = 25\text{A},$ $di/dt = 200\text{A}/\mu\text{s}$	-	460	-	ns
Reverse Recovery Current	I_{rr}		-	17	-	A
Reverse Recovery Charge	Q_{rr}		-	3600	-	nC



Fig. 1 FBSOA characteristics

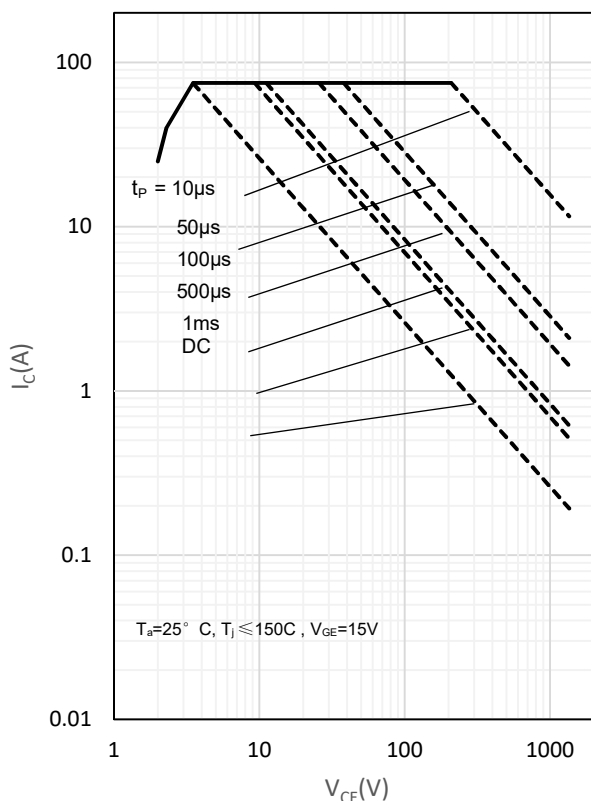


Fig. 2 Load Current vs. Frequency

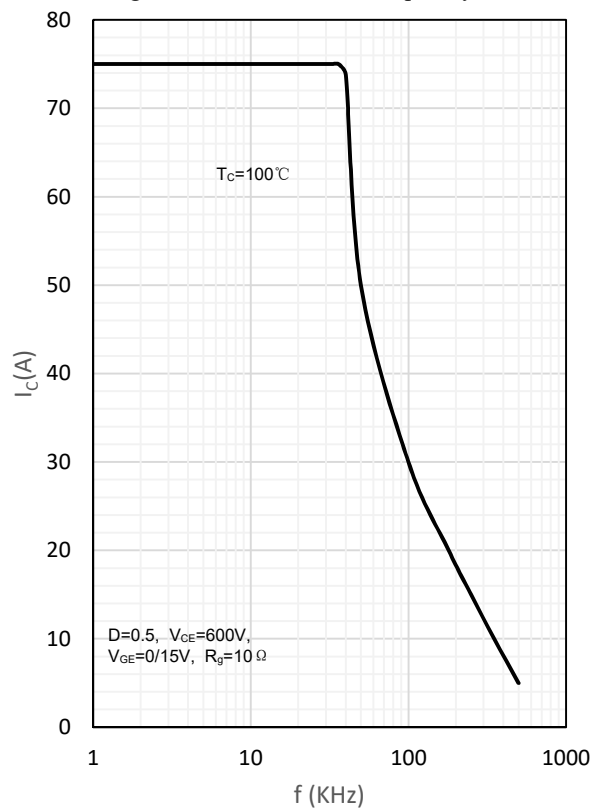


Fig. 3 Output characteristics

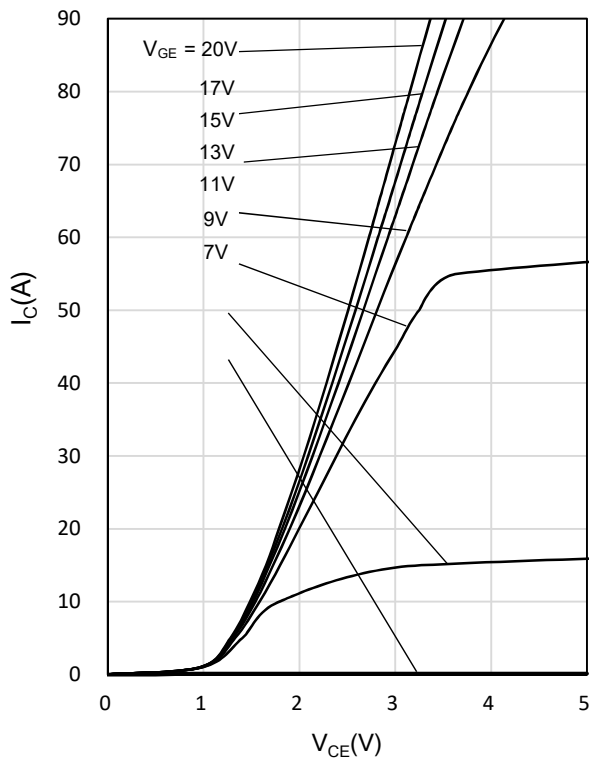


Fig. 4 Saturation voltage characteristics

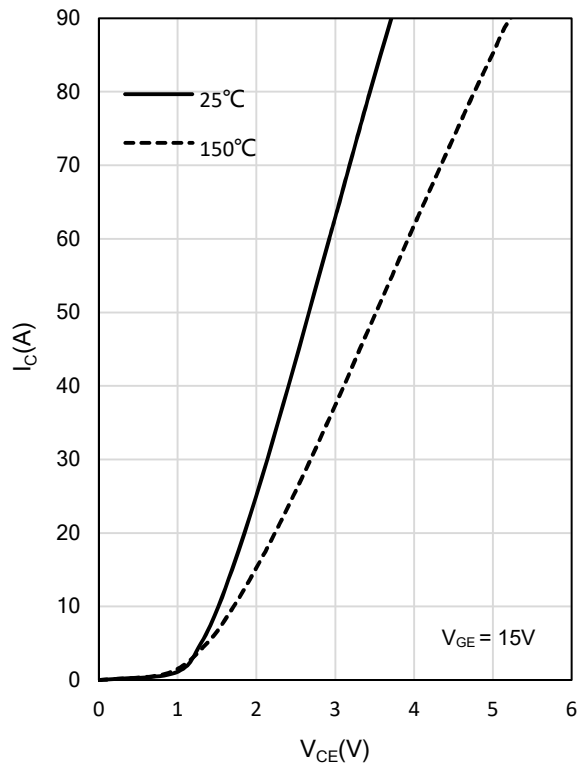




Fig. 5 Turn-off time vs. gate resistor

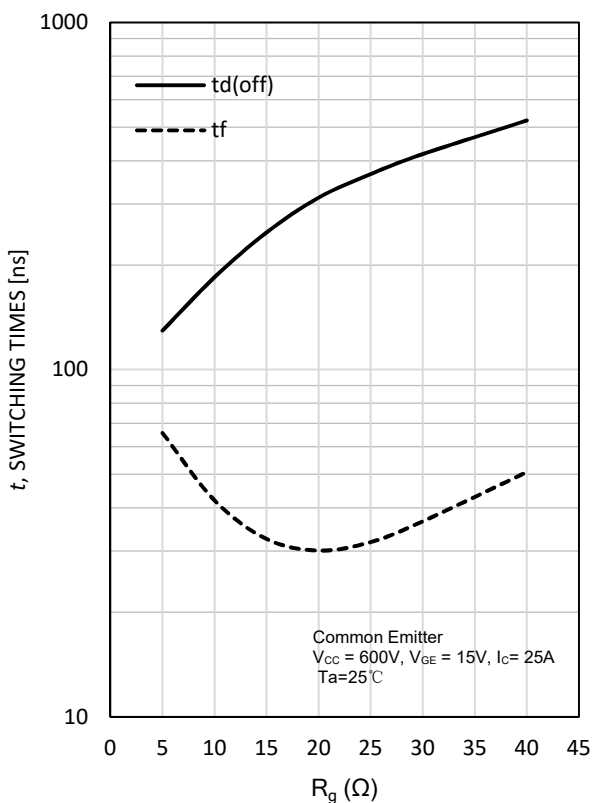


Fig. 6 Turn-off time vs. collector current

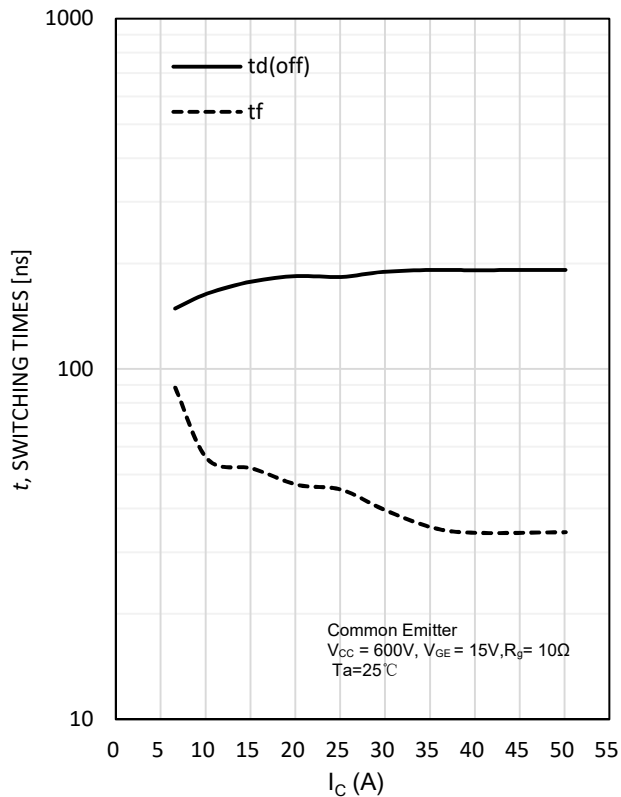


Fig. 7 Switching loss vs. gate resistor

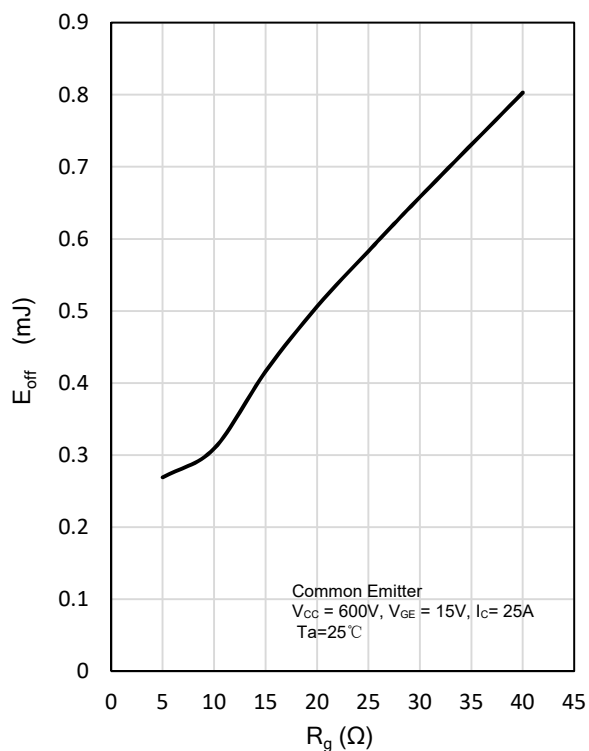


Fig. 8 Switching loss vs. collector current

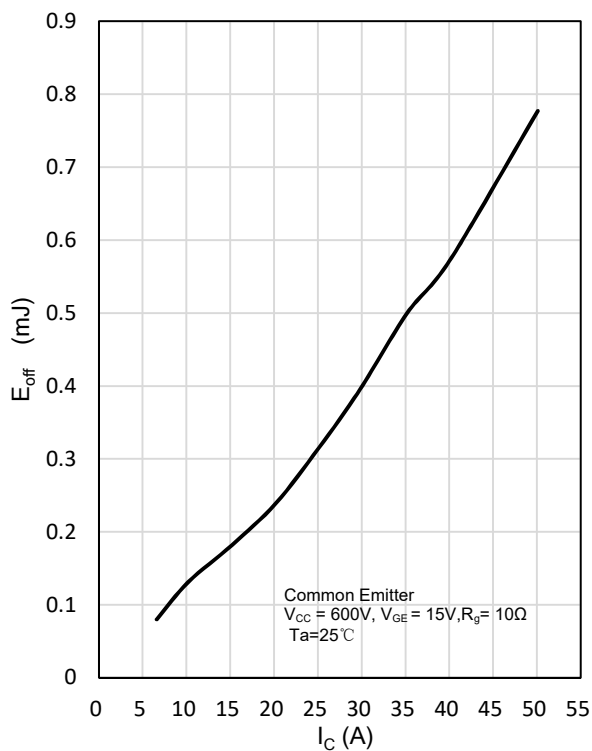




Fig. 9 Gate charge characteristics

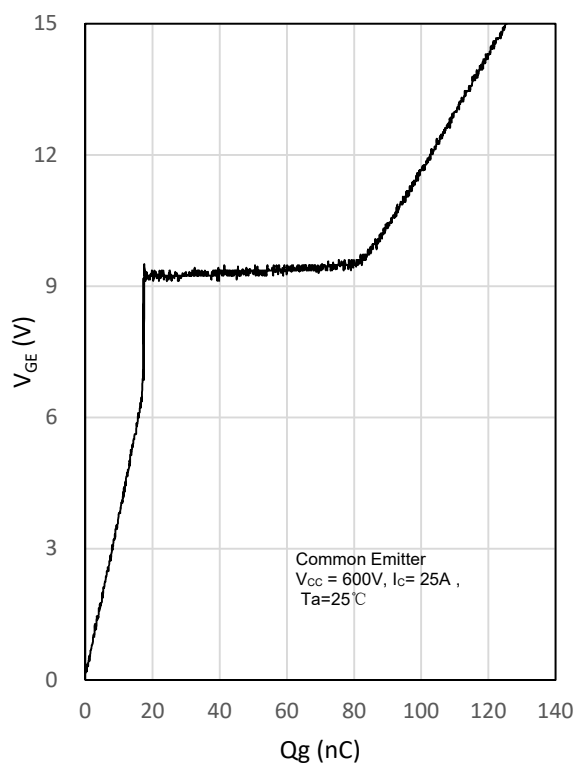
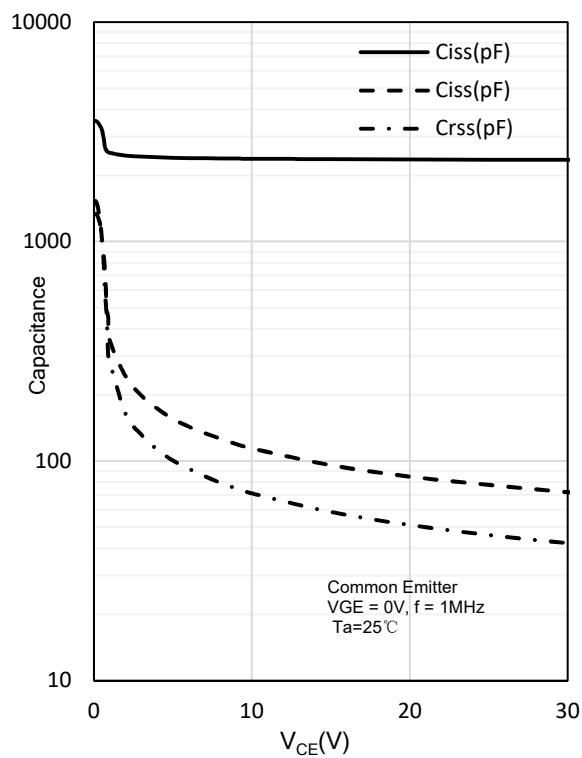
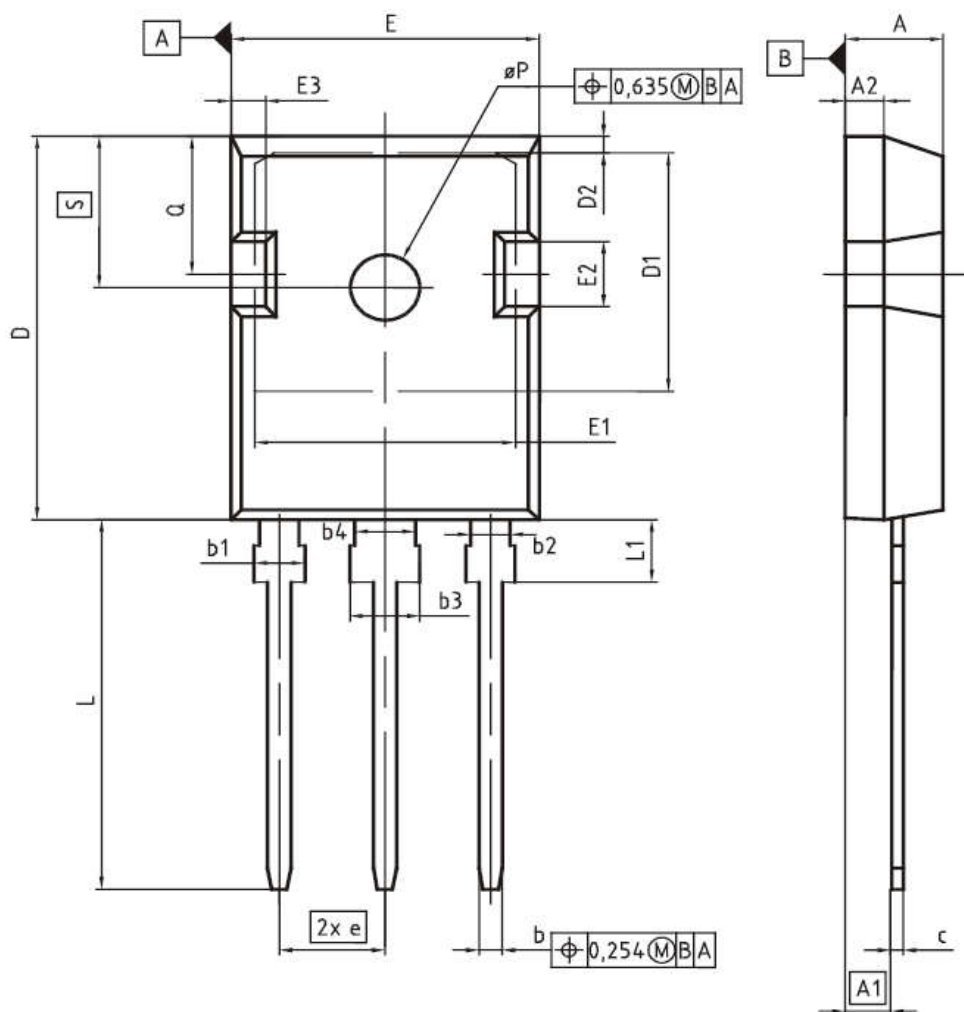


Fig. 10 Capacitance characteristics



**PG-TO247-3**

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44 (BSC)		0.214 (BSC)	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
øP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248